General Description

The WSP6020 is the highest performance trench N-ch MOSFETs with extreme high cell density , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The WSP6020meet the RoHS and Green Product requirement , 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

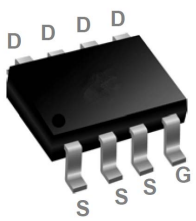
Product Summery

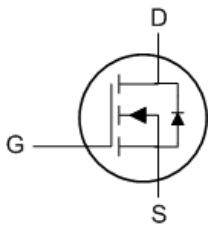
BVDSS	RDSON	ID
60V	7mΩ	18A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

SOP-8 Pin Configuration





Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ 10V[1]	18	A
I_D@T_C=70℃	Continuous Drain Current, V_{GS} @ 10V[1]	12	A
I_{DM}	Pulsed Drain Current[2]	72	A
EAS	Single Pulse Avalanche Energy[3]	196	mJ
I_{AS}	Avalanche Current	16	A
P_D@T_A=25℃	Total Power Dissipation[4]	2.5	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	150	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient [1]	---	72	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	---	1.2	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	60	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BVDSS Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	0.044	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=15A	---	7	9	mΩ
		V_{GS}=4.5V , I_D=10A	---	8	12	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.0	2.0	3.0	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-4.6	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=60V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=60V , V_{GS}=0V , T_J=55℃	---	---	100	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
Q_g	Total Gate Charge (10V)	V_{DS}=24V , V_{GS}=10V , I_D=10A	---	82	---	nC
Q_{gs}	Gate-Source Charge		---	13	---	
Q_{gd}	Gate-Drain Charge		---	17	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=30V , V_{GEN}=10V , R_G=6Ω I_D=4A ,R_L=30Ω	---	26	---	ns
T_r	Rise Time		---	125	---	
$T_{d(off)}$	Turn-Off Delay Time		---	58	---	
T_f	Fall Time		---	112	---	
C_{iss}	Input Capacitance	V_{DS}=15V , V_{GS}=0V , f=1MHz	---	3760	---	pF
C_{oss}	Output Capacitance		---	340	---	
C_{rss}	Reverse Transfer Capacitance		---	200	---	

Guaranteed Avalanche Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy[5]	V_{DD}=25V , L=0.1mH , I_{AS}=12A	---	196	---	mJ

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1.2	V
t_{rr}	Reverse Recovery Time	I_F=6.3A , dI/dt=100A/μs , T_J=25℃	---	38	---	nS
Q_{rr}	Reverse Recovery Charge		---	44	---	nC

Note :
1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper,t<10sec.
2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3.The EAS data shows Max. rating . The test condition is V_{DD}=25V,V_{GS}=10V,L=0.1mH,I_{AS}=12A
4.The power dissipation is limited by 150℃ junction temperature
5.The Min. value is 100% EAS tested guarantee.
6.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

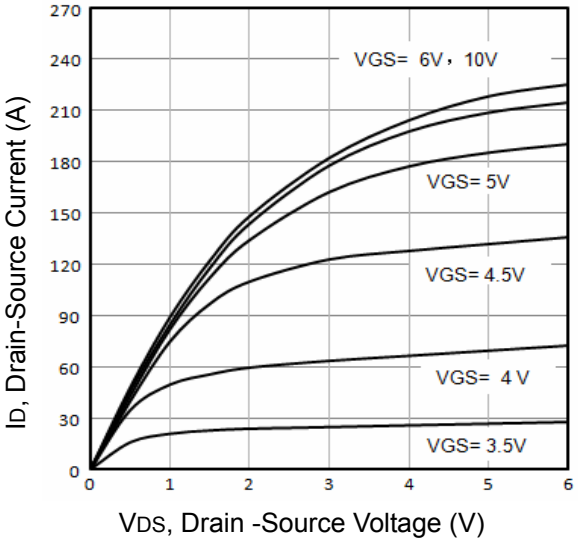


Fig1. Typical Output Characteristics

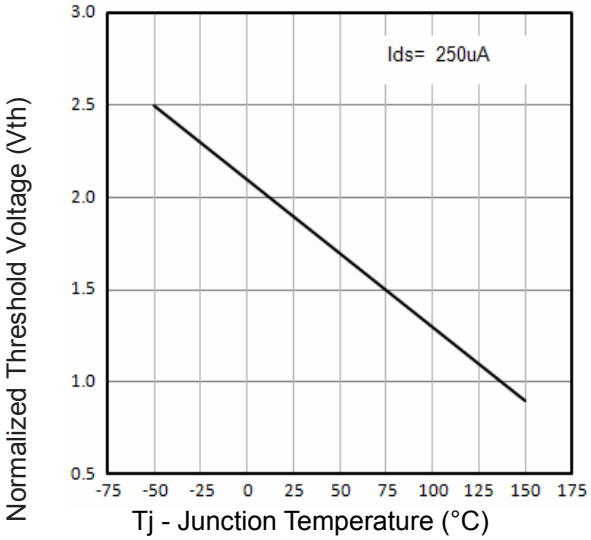


Fig2. Normalized Threshold Voltage Vs.

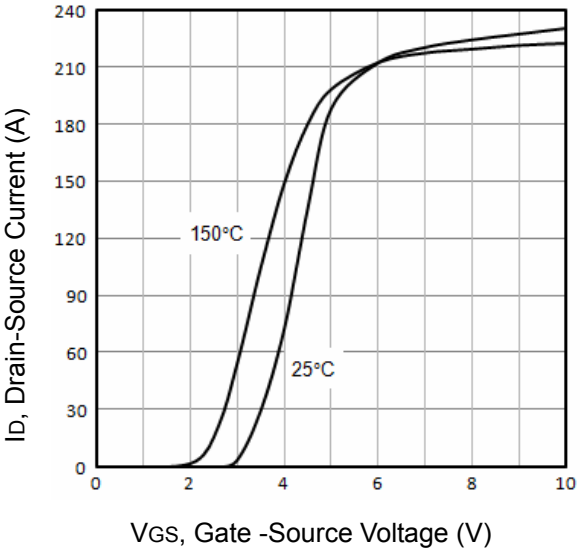


Fig3. Typical Transfer Characteristics

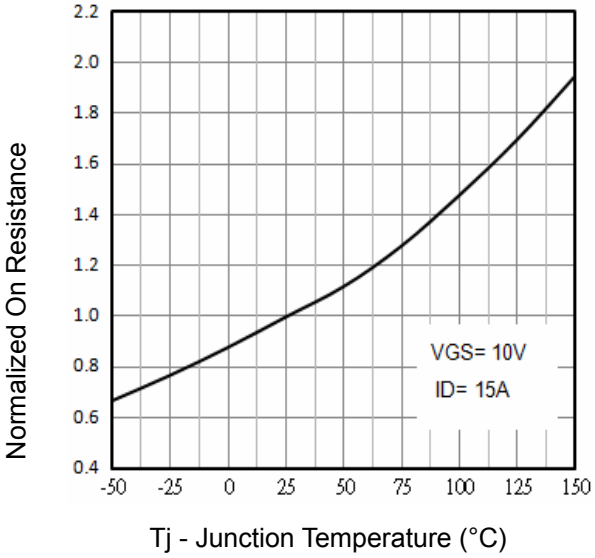


Fig4. Normalized On-Resistance Vs. Temperature

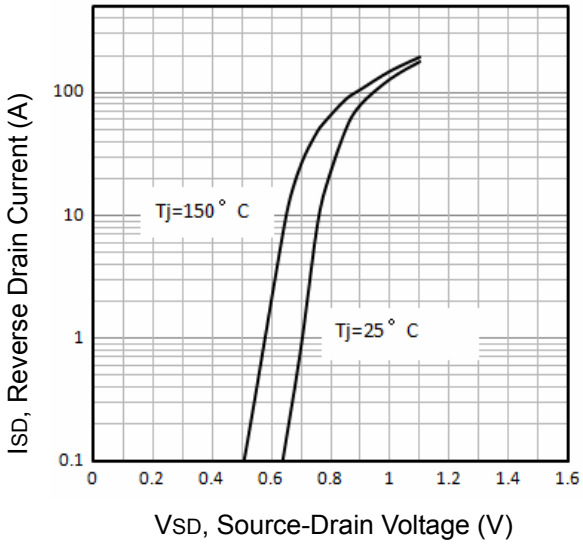


Fig5. Typical Source-Drain Diode Forward Voltage

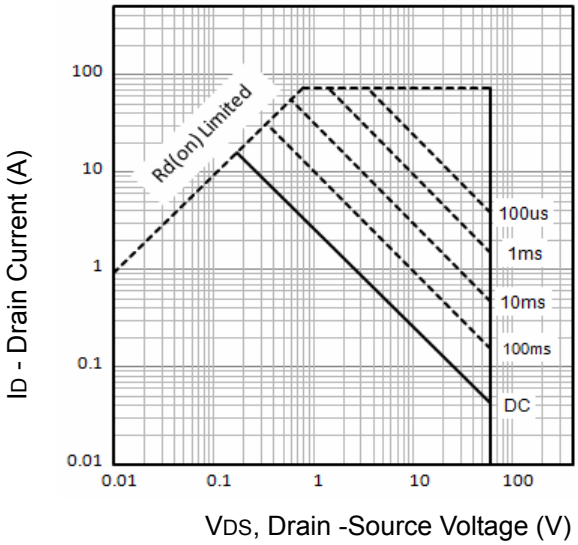
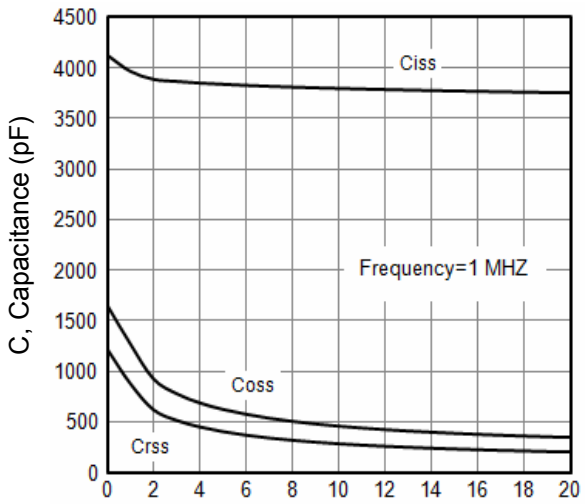
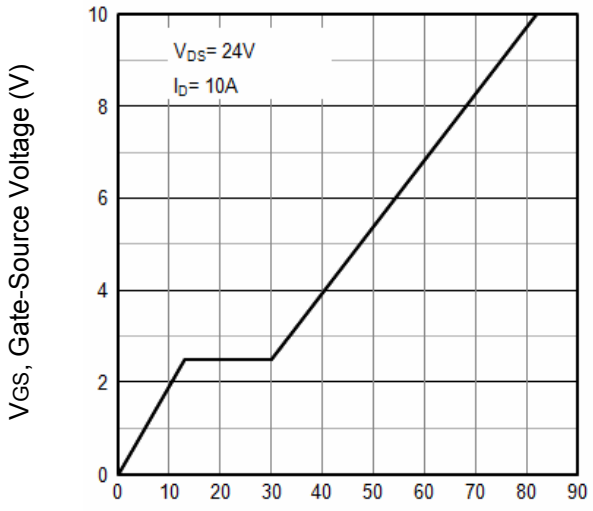


Fig6. Maximum Safe Operating Area



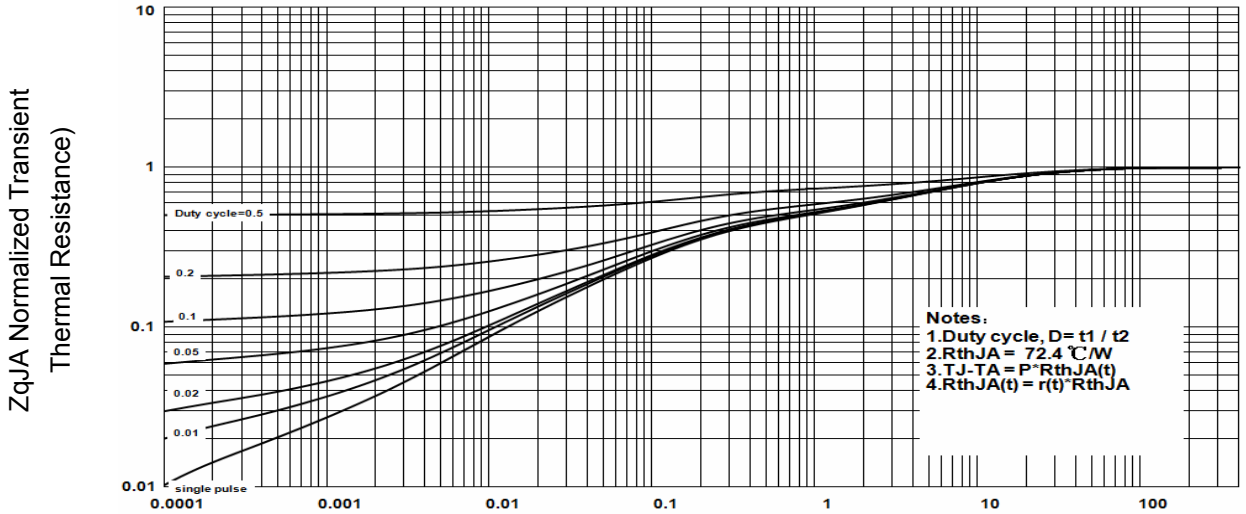
VDS , Drain-Source Voltage (V)

Fig7. Typical Capacitance Vs.Drain-Source Voltage



Qg -Total Gate Charge (nC)

Fig8. Typical Gate Charge Vs.Gate-Source Voltage



Pulse Width (s)

Figure 9: Normalized Maximum Transient Thermal Impedance

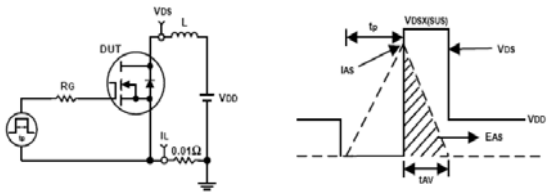


Fig10. Unclamped Inductive Test Circuit and waveforms

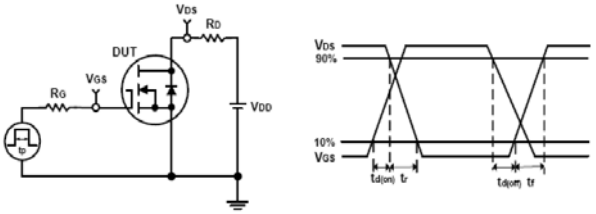
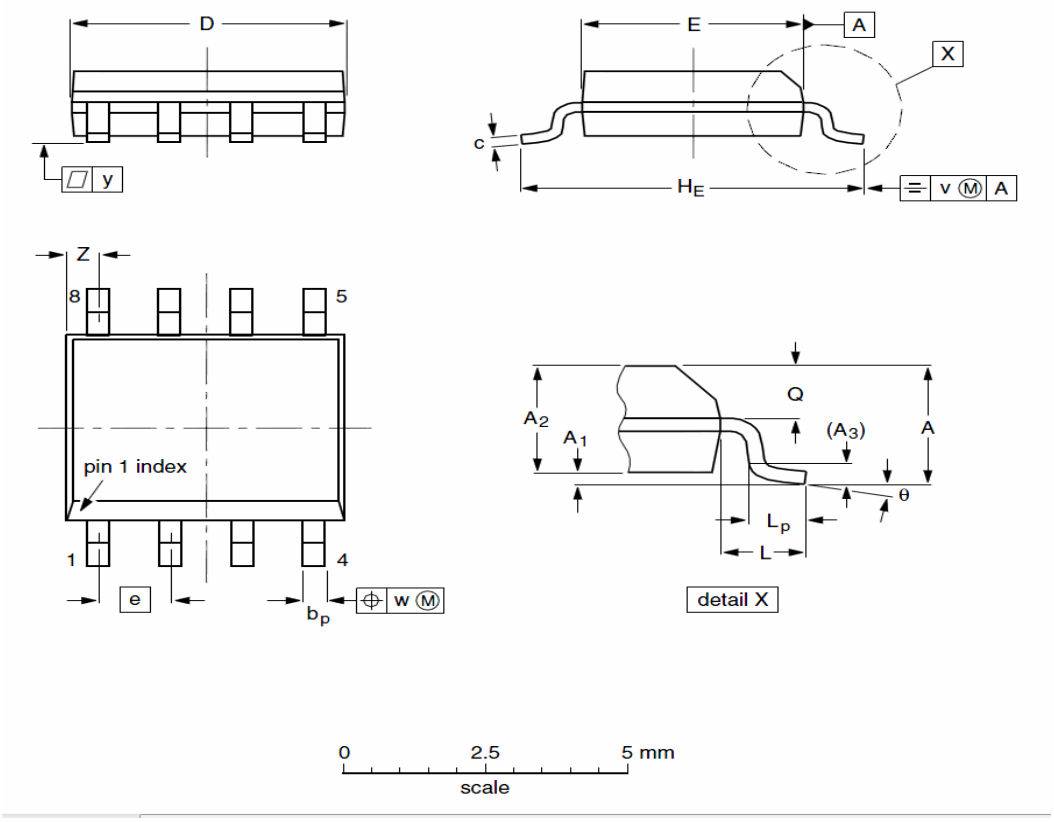


Fig11. Switching Time Test Circuit and waveforms

SOP8 Package Outline Data



DIMENSIONS (unit : mm)

Symbol	Min	Typ	Max	Symbol	Min	Typ	Max
A	--	1.75	--	**A_1**	0.10	0.18	0.25
A_2	1.25	1.35	1.45	**A_3**	--	0.25	--
b_p	0.36	0.42	0.49	**c**	0.19	0.22	0.25
D	4.80	4.92	5.00	**E**	3.80	3.90	4.00
e	--	1.27	--	**H_E**	5.80	5.98	6.20
L	--	1.05	--	**L_p**	0.40	0.68	1.00
Q	0.60	0.65	0.70	**v**	--	0.25	--
w	--	0.25	--	**y**	--	0.10	--
Z	0.30	0.50	0.70	**θ**	0°		8°

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